

IN THE SPECIFICATION

Please amend the Title at page 1, line 2, as follows:

MULTI-VALUE MAGNETIC RANDOM ACCESS MEMORY WITH STACKED
TUNNEL MAGNETORESISTANCE (TMR) ELEMENTS

Please amend the paragraph at page 17, lines 13-21, as follows:

Therefore, hereafter, the intensity of the current circulating through the current-driving line 24 (or magnetic field generated by the current) is further adjusted to write data DATA2 in the TMR layer TMR2 at the position of a white circle in FIG. 5. In this case, because the magnetic field does not have an intensity large enough to rewrite the data in the TMR layer TMR1, the data [[DATA2]] DATA1 is not overwritten in the TMR layer TMR1 but the data DATA1 is held.

Please amend the paragraph at page 30, lines 20-22, as follows:

FIGS. 18 and 19 show a device structure of the magnetic random access memory of the first example of the present invention.